



AC847BWQ_AC847CWQ

NPN SMALL SIGNAL TRANSISTOR IN SOT323

Description

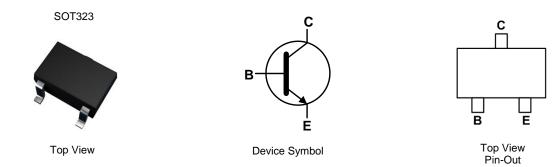
AC847BWQ and AC847CWQ Bipolar Junction Transistors (BJT) are designed to meet the stringent requirements of Automotive Applications.

Features

- Ideally Suited for Automatic Insertion
- Complementary PNP Types: AC857BWQ AC857CWQ
- For Switching and AF Amplifier Applications
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: SOT323
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.006 grams (Approximate)



Ordering Information (Notes 4 & 5)

Part Number	Compliance	Marking	Reel Size (inches)	Quantity Per Reel
AC847BWQ-7	Automotive	2D6	7	3,000
AC847BWQ-13	Automotive	2D6	13	10,000
AC847CWQ-7	Automotive	2D3	7	3,000

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

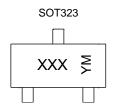
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html.

5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



XXX = Product Type Marking Code (Please see Ordering Information) YM = Date Code Marking Y or \overline{Y} = Year (ex: E = 2017) M or \overline{M} = Month (ex: 9 = September)

Date	Code	Key	

Notes:

Year	2017		2018	2019		2020	2021		2022	2023		2024
Code	E		F	G		Н			J	K		L
Month	Jan	Feb	Mar	Apr	Mav	Jun	Jul	Aug	Sep	Oct	Nov	Dec



AC847BWQ_AC847CWQ

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	50	V
Collector-Emitter Voltage	V _{CEO}	45	V
Emitter-Base Voltage	V _{EBO}	6	V
Continuous Collector Current	Ι _C	100	mA
Peak Collector Current	I _{CM}	200	mA
Peak Base Current	I _{BM}	200	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 6)	PD	200	mW
Thermal Resistance, Junction to Ambient	(Note 6)	R _{0JA}	625	°C/W
Operating and Storage Temperature Range	TJ, T _{STG}	-65 to +150	°C	

ESD Ratings (Note 7)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes: 6. For a device mounted on minimum recommended pad layout 1oz weight copper that is on a single-sided FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.

7. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



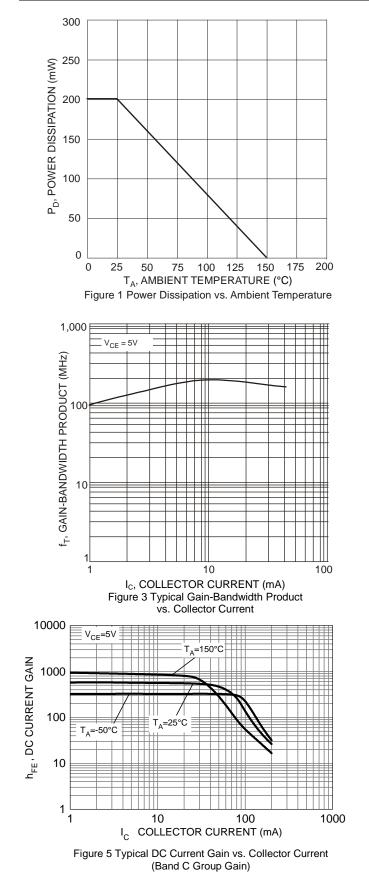
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

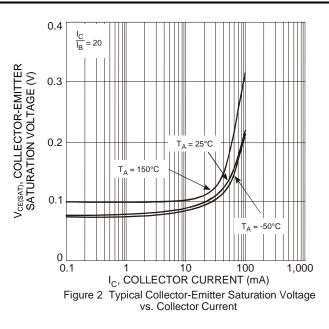
Characteristic				Min	Тур	Max	Unit	Test Condition	
Collector-Base Breakdown Voltage				50	_	—	V	I _C = 100μA	
Collector-Emitter Breakdown Voltage (Note 8)				45	_	—	V	I _C = 10mA	
Emitter-Base Breakdown Voltage			BV _{EBO}	6	_	—	V	I _E = 100μA	
DC Current Gain (Note 8)	Current Gain Group	В	h _{FE}	200	290	450		$V_{CE} = 5.0V, I_{C} = 2.0mA$	
	Current Gain Group	С	UFF F	420	520	800		$v_{CE} = 5.0v, v_{C} = 2.000A$	
Collector Cutoff Current			1			20	nA	$V_{CB} = 30V$	
Collector Catoli Carrent			I _{CBO}	_	_	5	μA	$V_{CB} = 30V, T_A = +150^{\circ}C$	
Collector-Emitter Saturation V	altaga (Nata 9)		V _{CE(SAT)}	_	90	250	mV	$I_{C} = 10 \text{mA}, I_{B} = 0.5 \text{mA}$	
Collector-Enlitter Saturation v	ollage (Note 6)				200	600	mv	$I_{C} = 100 \text{mA}, I_{B} = 5.0 \text{mA}$	
	(Nata 9)		V _{BE(ON)}	580	660	700	mV	$I_C = 2mA$, $V_{CE} = 5V$	
Base-Emitter Turn-On Voltage				_	_	770	mv	$I_{C} = 10 \text{mA}, V_{CE} = 5 \text{V}$	
	re (Nete O)			/BE(SAT) —	700			$I_{C} = 10mA, I_{B} = 0.5mA$	
Base-Emitter Saturation Volta	ge (Note 8)		VBE(SAT)		900	_	mV	$I_{C} = 100 \text{mA}, I_{B} = 5 \text{mA}$	
Output Capacitance			C _{OBO}	_	3	4.5	pF	V _{CB} = 10V, f = 1.0MHz	
Transition Frequency			f⊤	100	300	_	MHz	$V_{CE} = 5V, I_C = 10mA,$ f = 100MHz	
Noise Figure			NF	_	_	10	dB	$\begin{split} &V_{CE}=5V,\ I_C=200\mu A\\ &R_S=2k\Omega,\ f=1kHz\\ &\Delta f=200Hz \end{split}$	

Note: 8. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%.



Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)





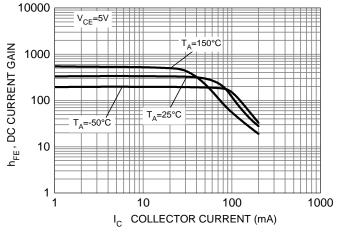


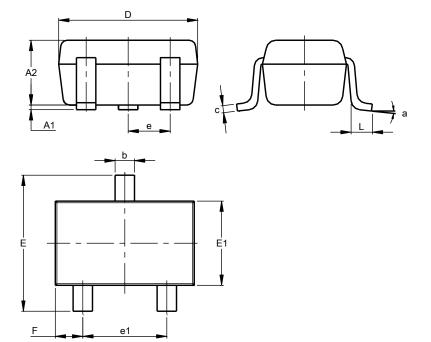
Figure 4 Typical DC Current Gain vs. Collector Current (Band B Group Gain)



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

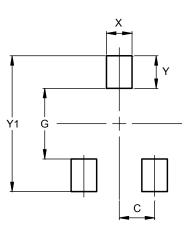
SOT323



	SOT323								
Dim	Min	Max	Тур						
A1	0.00	0.10	0.05						
A2	0.90	1.00	0.95						
b	0.25	0.40	0.30						
С	0.10	0.18	0.11						
D	1.80	2.20	2.15						
Е	2.00	2.20	2.10						
E1	1.15	1.35	1.30						
е	C).650 B	SC						
e1	1.20	1.40	1.30						
F	0.375	0.475	0.425						
L	0.25	0.40	0.30						
а	0°	8°							
All	Dimen	sions i	in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	0.650
G	1.300
Х	0.470
Y	0.600
Y1	2.500

SOT323



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